

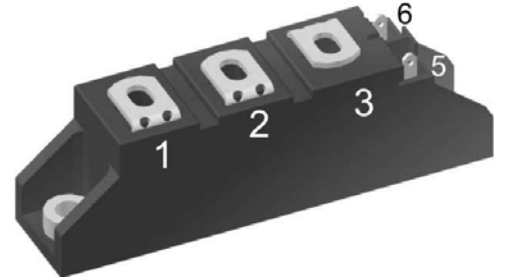
# Thyristor Module

 $V_{RRM} = 2 \times 800V$ 
 $I_{TAV} = 21A$ 
 $V_T = 1.32V$ 

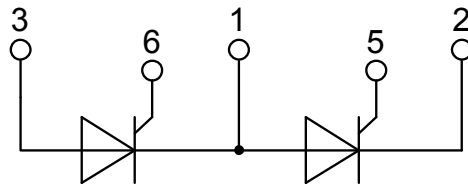
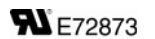
Phase leg

Part number

**MCC21-08io8B**



Backside: isolated



**Features / Advantages:**

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

**Applications:**

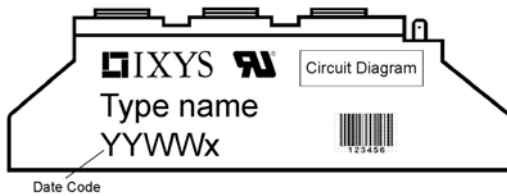
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

**Package: TO-240AA**

- Isolation Voltage: 3600V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

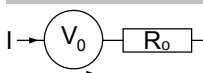
Thyristor				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			900	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			800	V	
$I_{RD}$	reverse current, drain current	$V_{RD} = 800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		100	$\mu\text{A}$	
		$V_{RD} = 800\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$		5	mA	
$V_T$	forward voltage drop	$I_T = 45\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.31	V	
					1.64	V	
		$I_T = 90\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$		1.32	V	
					1.74	V	
$I_{TAV}$	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 125^{\circ}\text{C}$		21	A	
$I_{T(RMS)}$	RMS forward current	180° sine			33	A	
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}\text{C}$		0.85	V	
$r_T$	slope resistance				15	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				1.1	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.20		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}\text{C}$		90	W	
$I_{TSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$		320	A	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		345	A	
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$		270	A	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		295	A	
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$		510	A <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		495	A <sup>2</sup> s	
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$		365	A <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		360	A <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		22	pF	
$P_{GM}$	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 125^{\circ}\text{C}$		10	W	
		$t_p = 300\text{ }\mu\text{s}$			5	W	
$P_{GAV}$	average gate power dissipation				0.5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 45\text{ A}$			150	A/ $\mu\text{s}$	
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.45\text{ A}/\mu\text{s};$ $I_G = 0.45\text{ A}; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 21\text{ A}$			500	A/ $\mu\text{s}$	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	$T_{VJ} = 125^{\circ}\text{C}$		1000	V/ $\mu\text{s}$	
$V_{GT}$	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1	V	
			$T_{VJ} = -40^{\circ}\text{C}$		1.2	V	
$I_{GT}$	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		65	mA	
			$T_{VJ} = -40^{\circ}\text{C}$		80	mA	
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$		0.2	V	
$I_{GD}$	gate non-trigger current				5	mA	
$I_L$	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		150	mA	
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu\text{s}$					
$I_H$	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$		100	mA	
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$		2	$\mu\text{s}$	
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu\text{s}$					
$t_q$	turn-off time	$V_R = 100\text{ V}; I_T = 15\text{ A}; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 20\text{ V}/\mu\text{s}; t_p = 300\text{ }\mu\text{s}$	$T_{VJ} = 125^{\circ}\text{C}$		150	$\mu\text{s}$	

Package TO-240AA				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			200	A
$T_{stg}$	storage temperature		-40		125	°C
$T_{VJ}$	virtual junction temperature		-40		125	°C
<b>Weight</b>				90		g
$M_D$	mounting torque		2.5		4	Nm
$M_T$	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
$V_{ISOL}$	isolation voltage	t = 1 second		3600		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000		V

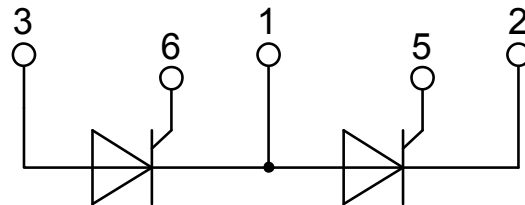
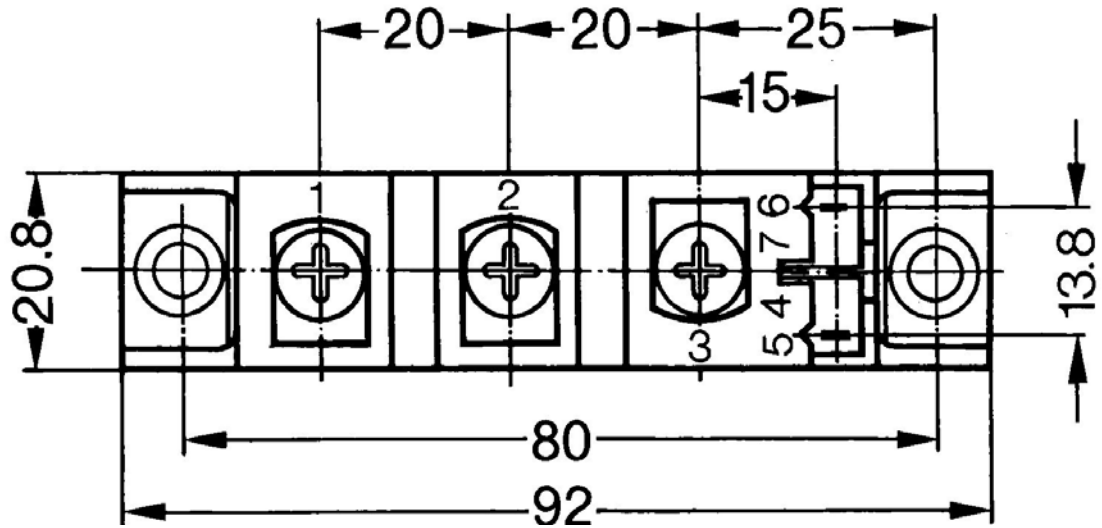
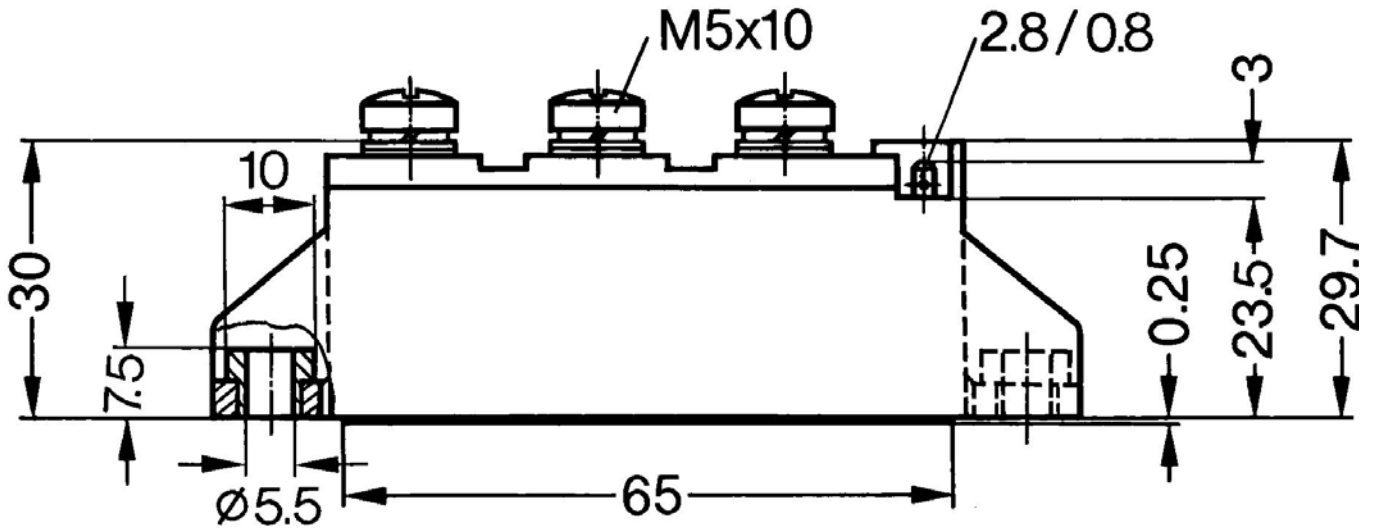


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC21-08io8B	MCC21-08io8B	Box	6	

Similar Part	Package	Voltage class
MCMA25P1200TA	TO-240AA-1B	1200
MCMA35P1200TA	TO-240AA-1B	1200

**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{VJ} = 125\text{ °C}$ 

**Thyristor**

$V_{0\ max}$	threshold voltage	0.85	V
$R_{0\ max}$	slope resistance *	13.8	mΩ



Thyristor

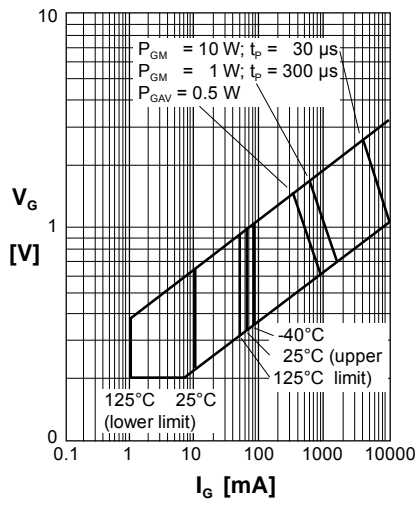


Fig. 1 Gate trigger characteristics

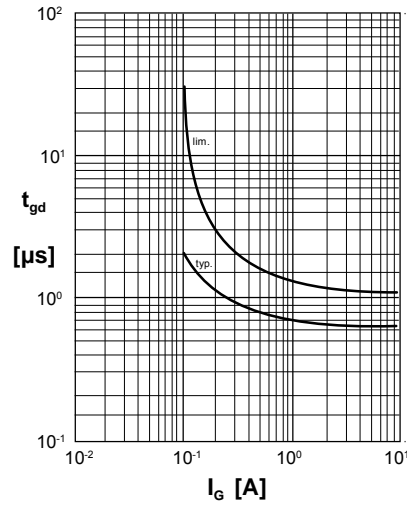


Fig. 2 Gate trigger delay time